



Si Avalanche Photodiode Preamplifier Module with Thermoelectric Cooler

CMC Electronics' 264-339820 series use a Silicon APD with a built-in preamplifier and a thermo-electric cooler (TEC), enabling optimum signal to noise performance.

The APD is coupled to a GaAs FET input transimpedance amplifier (TIA) in a 12-lead TO-8 package with an integrated thermoelectric cooler (TEC) allowing temperature control of the APD and easing stabilization of gain and optimized sensitivity.

The internal temperature can be monitored via an embedded thermal sensor close to the APD. The module is designed with either a 10 Ω output impedance which can be AC- or DC-coupled.

The amplifier has an overload input protection circuit that sustains high optical power exposure with a very fast recovery time.

Customizations such as bandwidth tuning, NEP screening, responsivity optimization and different temperature sensors are available upon request.



Features

- 500 μm Silicon APD
- 60 100 MHz Preamplifier Module
- Spectral Response: 550 1100 nm
- Low Noise Equivalent Power (NEP)
- Overload Input Protection circuit
- High efficiency TEC
- Hermetically Sealed TO-8 Package



Applications

- Laser Range Finding
- LIDAR
- Instrumentation
- Laser Profiling
- Industrial
- Photometry

264-339820 Series

Silicon Avalanche Photodiode Preamplifier Module with TEC

Table 1. Electro-Optical Characteristics

Unless otherwise specified: T_A = 25°C, V_POS = 5.0 V, V_NEG = -5.0 V, R_L = 100 Ω , λ = 1064 nm +/- 10 nm, Cooler OFF (Externally AC-coupled through 4.7 μ F)

Parameter	Min.	Тур.	Max.	Units
Active area		500		μm
Operating Voltage (Note 1)	150	225	300	V
Temperature coefficient of V _{OP}		0.6	1.5	V/°C
ADP dark current		7	50	nA
Responsivity	1000			kV/W
Noise equivalent power (Note 2) 1064 nm [T _{case} =25°C] 1064 nm [T _{case} =85°C]	75	100 220	120 575	fW/vHz fW/vHz
Output impedance		10		Ω
Bandwidth	60	80		MHz
Rise time (10-90%)		6		ns
Fall time (90-10%)		6		ns
Linear output voltage swing (Pulse)	1.5	2.5	4.0	V
Output offset voltage	-0.75	-0.45	0	V
Thermal sensor (NTC thermistor) Impedance	8.5	9.4	11	kΩ
Accuracy		±5		%
Overload recovery for optical power input signal of 1 mW, 20 ns pulse width: $V_{out} \rightarrow 200$ ns after pulse start			3000	mV
$V_{\text{out}} \rightarrow 1 \mu \text{s} \text{after pulse start}$			20	mV
Hybrid Supply current V_POS (pin 10)	25	30	40	mA
V_NEG (pin 11)	-20	-15	-10	mA

Notes: 1. Each APD receivers will have its individual Vop (provided on its production tests report).

Table 2. Absolute-Maximum Ratings, Limiting Values

Parameter	Min.	Max.	Units
APD breakdown, Maximum voltage [HV_POSITIVE (pin7)] (Note 1)	1.0).	450	V
Recommended overcurrent limit		100	μΑ
Input Voltage Positive Supply [V_POS (+5V) (pin10)]	+4.8	+6.0	V
Input Voltage Negative Supply [V_NEG (-5V) (pin11)]	-4.8	-6.0	V
Maximum Optical Power, M = 100		300	μW
Maximum Optical Power, M = 1		30	mW
TEC Current (between TEC+ (pin3) and TEC- (pin2))	-1.75	1.75	А
Operating Temperature	-40	85	°C
Storage Temperature	-55	125	°C

Note: 1. Absolute maximum over the product Temperature Operating Range (-40°C to +85°C).

^{2.} NEP values for +85°C are by design and are for reference only. No test values provided on individual test reports. Integration of the noise calculation is based on minimum bandwidth.

Figure 1. CMC 264-339820 Series block diagram

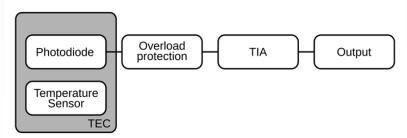
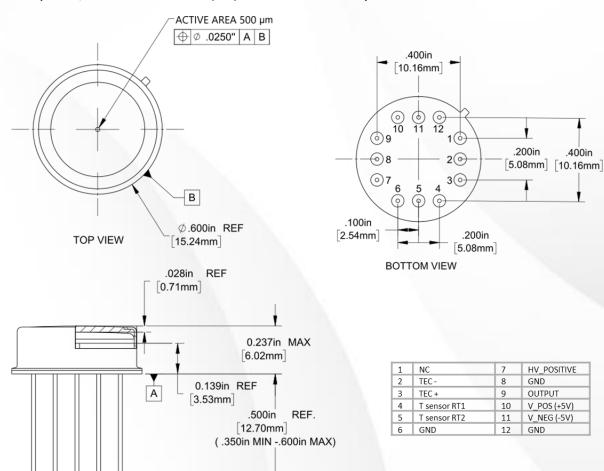


Figure 2. Package Dimension and Pinout

Unless otherwise specified, dimensions are in inches (mm) and are for reference only.



VAR Options

-001 Silicon APD 500 μm, 60-100 MHz TIA, TEC

For more information, visit www.cmcelectronics.ca/optoelectronics
Or email us at opto@cmcelectronics.ca

For information purposes only. To accommodate product improvements, specifications are subject to change without notice.

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